



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92S Plastic-Encapsulate Transistors

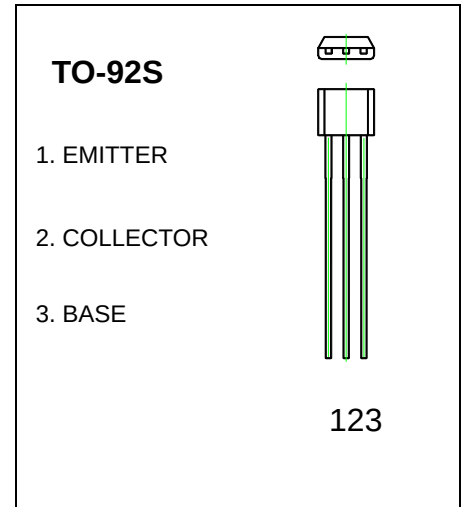
2SA1048 TRANSISTOR (PNP)

FEATURES

- High voltage: $V_{CEO}=-50V(\text{Min.})$
- High h_{FE} : $h_{FE}=70\sim400$
- Low noise: $NF=1dB(\text{Typ.}), 10dB(\text{Max.})$
- Complementary to 2SC2458

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector- Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.15	A
P_C	Collector Power Dissipation	0.2	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.3	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-1mA$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			7	pF
Noise figure	NF	$V_{CE}=-6V, I_C=-0.1mA, f=1KHz, R_g=10K\Omega$			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR
Range	70-140	120-240	200-400

Typical Characteristics

2SA1048

